2010 International Symposium on Dry Process

Program

Thursday, November 11, 2010

Opening Remarks (9:30–9:35, Digital Hall) N. Itabashi

Award Ceremony (9:35–9:50, Digital Hall) Presenter: T. Ohiwa

Session A Solar Cell, Green Technology (9:50–12:45, Digital Hall)

Chairpersons: Y. Shimogaki, K. Nishioka

[A-1] **<Invited>** Research for Photovoltaics: Cost Reduction of Solar Energy through Comprehensive Researches from Materials to Large Scale PV Systems **9:50–10:30**
M. Kondo[1,2], H. Sai[1], T. Matsui[1] ([1]AIST, [2]Tokyo Inst. of Technology) 1

[A-2] **<Invited>** Atmospheric-Pressure Plasma Technology for the High-Rate and Low-Temperature Deposition of Si Thin Films **10:30–11:10**
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D.-Y. Lee[1], C. Yang[1], H.-M. Li[1], W.J. Yoo[1], Y.J. Park[2], J.M. Kim[2] ([1]Sungkyunkwan Univ., [2]Samsung Electronics Co., Ltd.) 5

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[H-4] Mechanisms of Selective Etching for Magnetic Thin Films by Reactive Plasmas for MRAM Applications **16:05–16:25**
K. Karahashi, T. Ito, S. Hamaguchi (Osaka Univ.) 183

Break (16:25–16:40)

Session J Plasma Induced Damage (16:40–18:00, Digital Hall)

Chairpersons: M. Nakamura, H. Hayashi

[J-1] Trade-Off Relationship between Si Recess and Defect Density Formed by Plasma-Induced Damage in Planar MOSFETs and the Optimization Strategies **16:40–17:00**
K. Eriguchi, Y. Nakakubo, A. Matsuda, Y. Takao, K. Ono (Kyoto Univ.) 185

[J-2] Si Recess of Poly-Si Gate Etching: Damage Enhanced by Ion Assisted Oxygen Diffusion **17:00–17:20**
T. Ito[1], K. Karahashi[1], M. Fukasawa[2], T. Tatsumi[2], S. Hamaguchi[1]
([1]Osaka Univ., [2]Sony Corp.) 187

[J-3] Comparative Study of Plasma-Charging Damage in High-k Dielectric and p-n Junction and their Effects on Off-State Leakage Current of MOSFETs **17:20–17:40**
M. Kamei, Y. Takao, K. Eriguchi, K. Ono (Kyoto Univ.) 189

[J-4] Advanced Contactless Analysis of Plasma-Induced Damage on Si by Temperature-Controlled Photoreflectance Spectroscopy **17:40–18:00**
A. Matsuda, Y. Nakakubo, Y. Takao, K. Eriguchi, K. Ono (Kyoto Univ.) 191

Closing Remark (18:00–18:05, Digital Hall)
K. Kurihara